



128K x 8 Static RAM

Features

- **Low voltage range:**
 - 2.7V–3.6V (CY62128V)
 - 2.3V–2.7V (CY62128V25)
 - 1.6V–2.0V (CY62128V18)
- **Low active power and standby power**
- **Easy memory expansion with CE and OE features**
- **TTL-compatible inputs and outputs**
- **Automatic power-down when deselected**
- **CMOS for optimum speed/power**

Functional Description

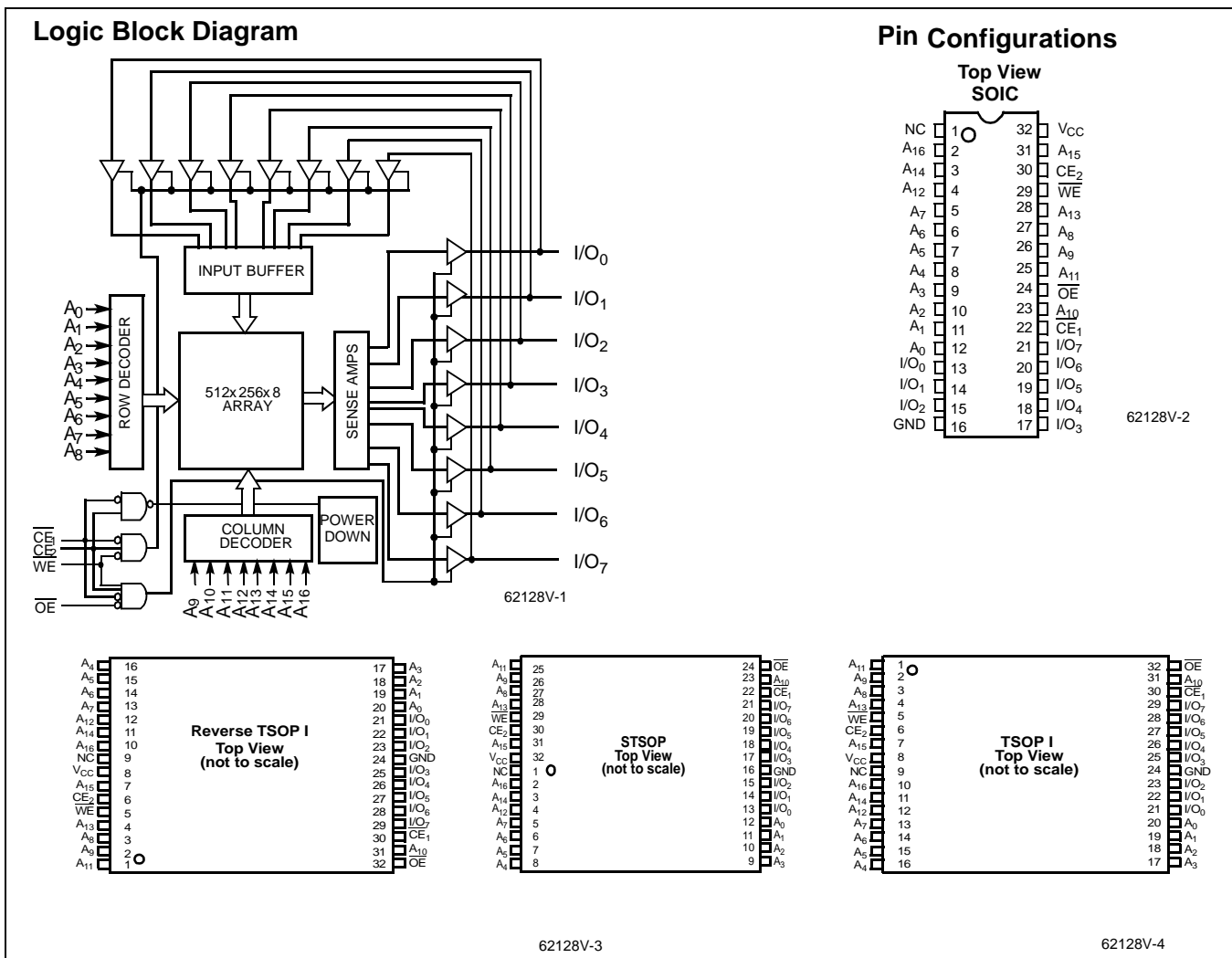
The CY62128V family is composed of three high-performance CMOS static RAMs organized as 131,072 words by 8 bits. Easy memory expansion is provided by an active LOW Chip Enable (\overline{CE}_1), an active HIGH Chip Enable (CE_2), an active

LOW Output Enable (\overline{OE}) and three-state drivers. These devices have an automatic power-down feature, reducing the power consumption by over 99% when deselected. The CY62128V family is available in the standard 450-mil-wide SOIC, 32-lead TSOP-I, and STSOP packages.

Writing to the device is accomplished by taking Chip Enable one (\overline{CE}_1) and Write Enable (\overline{WE}) inputs LOW and the Chip Enable two (CE_2) input HIGH. Data on the eight I/O pins (I/O_0 through I/O_7) is then written into the location specified on the address pins (A_0 through A_{16}).

Reading from the device is accomplished by taking Chip Enable one (\overline{CE}_1) and Output Enable (\overline{OE}) LOW while forcing Write Enable (\overline{WE}) and Chip Enable two (CE_2) HIGH. Under these conditions, the contents of the memory location specified by the address pins will appear on the I/O pins.

The eight input/output pins (I/O_0 through I/O_7) are placed in a high-impedance state when the device is deselected (\overline{CE}_1 HIGH or CE_2 LOW), the outputs are disabled (\overline{OE} HIGH), or during a write operation (\overline{CE}_1 LOW, CE_2 HIGH, and \overline{WE} LOW).



Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature -65°C to +150°C
 Ambient Temperature with Power Applied..... -55°C to +125°C
 Supply Voltage to Ground Potential (Pin 28 to Pin 14) -0.5V to +4.6V
 DC Voltage Applied to Outputs in High Z State^[1] -0.5V to $V_{CC} + 0.5V$
 DC Input Voltage^[1] -0.5V to $V_{CC} + 0.5V$

Output Current into Outputs (LOW)..... 20 mA
 Static Discharge Voltage >2001V (per MIL-STD-883, Method 3015)
 Latch-Up Current..... >200 mA

Operating Range

Range	Ambient Temperature	V_{CC}
Commercial	0°C to +70°C	1.6V to 3.6V
Industrial	-40°C to +85°C	1.6V to 3.6V

Product Portfolio

Product	V_{CC} Range			Speed	Power Dissipation (Commercial)			
	Min.	Typ. ^[2]	Max.		Operating (I_{CC})		Standby (I_{SB2})	
					Typ. ^[2]	Maximum	Typ. ^[2]	Maximum
CY62128V	2.7V	3.0V	3.6V	55, 70 ns	20 mA	40 mA	0.4 μ A	100 μ A (XL = 10 μ A)
CY62128V25	2.3V	2.5V	2.7V	100 ns	15 mA	20 mA	0.3 μ A	50 μ A (LL = 12 μ A)
CY62128V18	1.6V	1.8V	2.0V	200 ns	10 mA	15 mA	0.3 μ A	30 μ A (LL = 10 μ A)

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions	CY62128V-55/70			Unit	
			Min.	Typ. ^[2]	Max.		
V_{OH}	Output HIGH Voltage	$V_{CC} = \text{Min.}, I_{OH} = -1.0 \text{ mA}$	2.4			V	
V_{OL}	Output LOW Voltage	$V_{CC} = \text{Min.}, I_{OL} = 2.1 \text{ mA}$			0.4	V	
V_{IH}	Input HIGH Voltage		2		$V_{CC} + 0.5V$	V	
V_{IL}	Input LOW Voltage		-0.5		0.8	V	
I_{IX}	Input Load Current	$GND \leq V_I \leq V_{CC}$	-1	± 1	+1	μ A	
I_{OZ}	Output Leakage Current	$GND \leq V_O \leq V_{CC}$, Output Disabled	-1	± 1	+1	μ A	
I_{CC}	V_{CC} Operating Supply Current	$V_{CC} = \text{Max.}, I_{OUT} = 0 \text{ mA}, f = f_{MAX} = 1/t_{RC}$	Com'l, 70 ns	L	20	40	mA
				LL, XL	20	40	
			Ind'l, 55 ns	LL	23	50	
				Ind'l, 70 ns	L	20	
I_{SB1}	Automatic CE Power-Down Current—TTL Inputs	Max. V_{CC} , $\overline{CE} \geq V_{IH}$, $V_{IN} \geq V_{IH}$ or $V_{IN} \leq V_{IL}$, $f = f_{MAX}$	Com'l, 70 ns	L	15	300	μ A
				LL, XL	15	300	
			Com'l, 55 ns	LL	17	350	
				Ind'l	L	15	
LL	15	300					

Notes:

- V_{IL} (min.) = -2.0V for pulse durations of less than 20 ns.
- Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at $V_{CC} = V_{CC} \text{ Typ.}, T_A = 25^\circ\text{C}$.

Electrical Characteristics Over the Operating Range (continued)

Parameter	Description	Test Conditions	CY62128V-55/70			Unit	
			Min.	Typ. ^[2]	Max.		
I _{SB2}	Automatic CE Power-Down Current—CMOS Inputs	Max. V _{CC} , CE ≥ V _{CC} - 0.3V V _{IN} ≥ V _{CC} - 0.3V or V _{IN} ≤ 0.3V, f = 0	Com'l	L	0.4	100	μA
				LL		15	μA
				XL		10	μA
			Ind'l	L	0.4	100	μA
				LL		30	μA

Electrical Characteristics Over the Operating Range

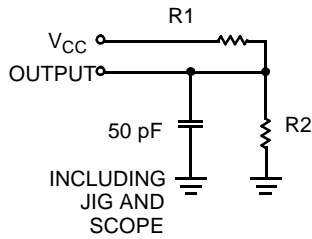
Parameter	Description	Test Conditions	CY62128V25-100			CY62128V18-200			Unit	
			Min.	Typ. ^[2]	Max.	Min.	Typ. ^[2]	Max.		
V _{OH}	Output HIGH Voltage	V _{CC} = Min., I _{OH} = -0.1 mA	2.4			0.8* V _{CC}			V	
V _{OL}	Output LOW Voltage	V _{CC} = Min., I _{OL} = 0.1 mA			0.4			0.2	V	
V _{IH}	Input HIGH Voltage		2		V _{CC} +0.5	0.7* V _{CC}		V _{CC} +0.3	V	
V _{IL}	Input LOW Voltage		-0.5		0.8	-0.5		0.3* V _{CC}	V	
I _{IX}	Input Load Current	GND ≤ V _I ≤ V _{CC}	-1	±1	+1	-1	±0.1	+1	μA	
I _{OZ}	Output Leakage Current	GND ≤ V _O ≤ V _{CC} , Output Disabled	-1	±1	+1	-1	±0.1	+1	μA	
I _{CC}	V _{CC} Operating Supply Current	V _{CC} = Max., I _{OUT} = 0 mA, f = f _{MAX} = 1/t _{RC}	L		15	20		10	15	mA
			LL							
I _{SB1}	Automatic CE Power-Down Current—TTL Inputs	Max. V _{CC} , $\overline{CE} \geq V_{IH}$, V _{IN} ≥ V _{IH} or V _{IN} ≤ V _{IL} , f = f _{MAX}	L		15	300		5	100	μA
			LL							
I _{SB2}	Automatic CE Power-Down Current—CMOS Inputs	Max. V _{CC} , CE ≥ V _{CC} - 0.3V V _{IN} ≥ V _{CC} - 0.3V or V _{IN} ≤ 0.3V, f = 0	L		0.4	50		0.4	30	μA
			LL			12			10	μA
		Indust'l Temp Range	LL			24			20	μA

Capacitance^[3]

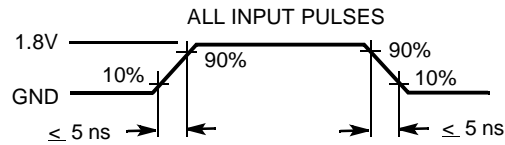
Parameter	Description	Test Conditions	Max.	Unit
C _{IN}	Input Capacitance	T _A = 25°C, f = 1 MHz, V _{CC} = 3.0V	6	pF
C _{OUT}	Output Capacitance		8	pF

Note:

3. Tested initially and after any design or process changes that may affect these parameters.

AC Test Loads and Waveforms


62128V-5



62128V-6

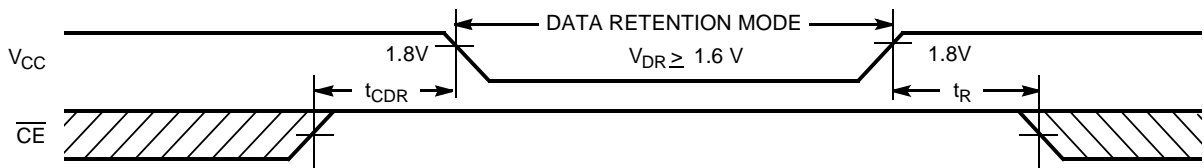
Equivalent to: THÉVENIN EQUIVALENT



Parameters	3.3V	2.5V	1.8V	Unit
R1	1213	15909	10800	Ohms
R2	1378	4487	4154	Ohms
R_{TH}	645	3500	3000	Ohms
V_{TH}	1.75V	0.55V	0.50V	Volts

Data Retention Characteristics (Over the Operating Range)

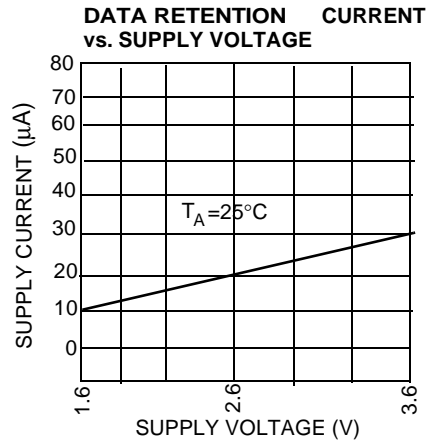
Parameter	Description	Conditions ^[4]	Min.	Typ. ^[2]	Max.	Unit	
V_{DR}	V_{CC} for Data Retention		1.6			V	
I_{CCDR}	Data Retention Current	Com'l	L	$V_{CC} = 2V$ $CE \ge V_{CC} - 0.3V$, $V_{IN} \ge V_{CC} - 0.3V$ or $V_{IN} \le 0.3V$ No input may exceed $V_{CC} + 0.3V$	0.4	10	μA
			LL, XL			10	μA
		Ind'l	L			20	μA
			LL			20	μA
$t_{CDR}^{[3]}$	Chip Deselect to Data Retention Time		0			ns	
t_R	Operation Recovery Time		t_{RC}			ns	

Data Retention Waveform


C62128V-7

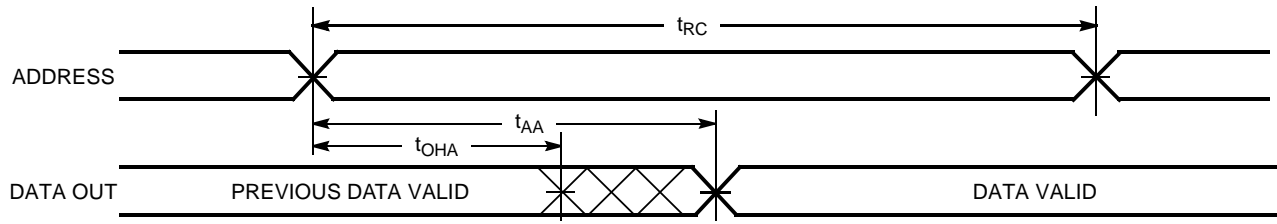
Note:

4. No input may exceed $V_{CC} + 0.3V$.

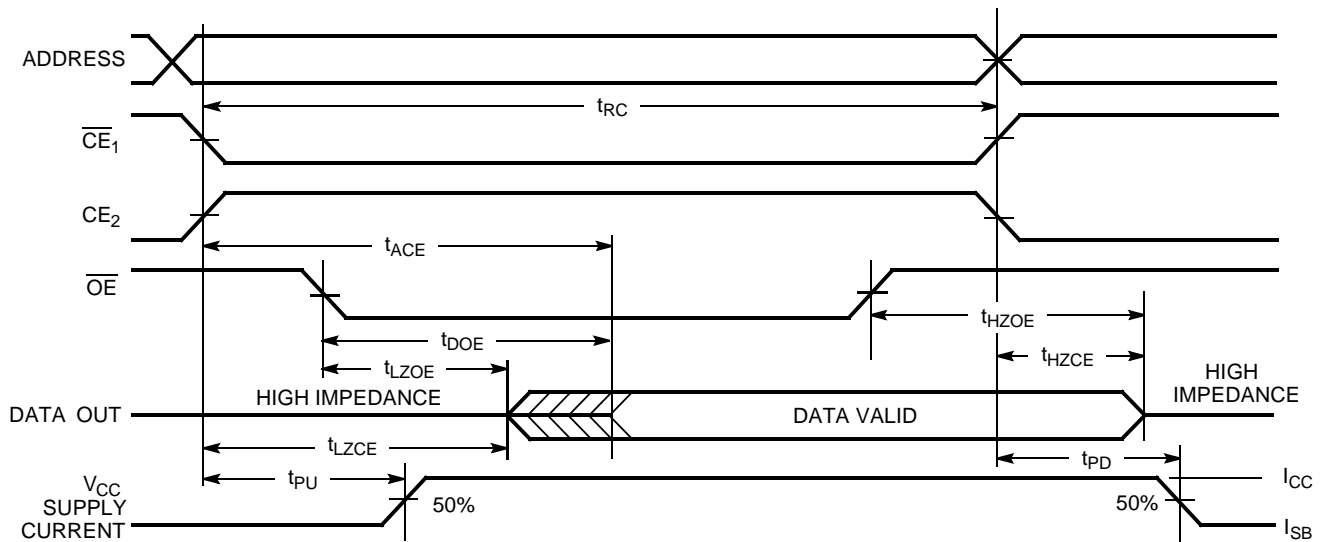
Data Retention Current Graph (for "L" version only)

Switching Characteristics Over the Operating Range^[5]

Parameter	Description	62128V-55		62128V-70		62128V25-100		62128V18-200		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
READ CYCLE										
t _{RC}	Read Cycle Time	55		70		100		200		ns
t _{AA}	Address to Data Valid		55		70		100		200	ns
t _{OHA}	Data Hold from Address Change	5		10		10		10		ns
t _{ACE}	\overline{CE} LOW to Data Valid		55		70		100		200	ns
t _{DOE}	\overline{OE} LOW to Data Valid		20		35		75		125	ns
t _{LZOE}	\overline{OE} LOW to Low Z ^[6]	10		10		10		10		ns
t _{HZOE}	\overline{OE} HIGH to High Z ^[6, 7]		20		25		50		75	ns
t _{LZCE}	\overline{CE} LOW to Low Z ^[6]	10		10		10		10		ns
t _{HZCE}	\overline{CE} HIGH to High Z ^[6, 7]		20		25		50		75	ns
t _{PU}	\overline{CE} LOW to Power-Up	0		0		0		0		ns
t _{PD}	\overline{CE} HIGH to Power-Down		55		70		100		200	ns
WRITE CYCLE^[8, 9]										
t _{WC}	Write Cycle Time	55		70		100		200		ns
t _{SCE}	\overline{CE} LOW to Write End	45		60		100		190		ns
t _{AW}	Address Set-Up to Write End	45		60		100		190		ns
t _{HA}	Address Hold from Write End	0		0		0		0		ns
t _{SA}	Address Set-Up to Write Start	0		0		0		0		ns
t _{PWE}	\overline{WE} Pulse Width	45		55		90		125		ns
t _{SD}	Data Set-Up to Write End	25		30		60		100		ns
t _{HD}	Data Hold from Write End	0		0		0		0		ns
t _{HZWE}	\overline{WE} LOW to High Z ^[6, 7]		20		25		50		100	ns
t _{LZWE}	\overline{WE} HIGH to Low Z ^[6]	5		5		10		15		ns

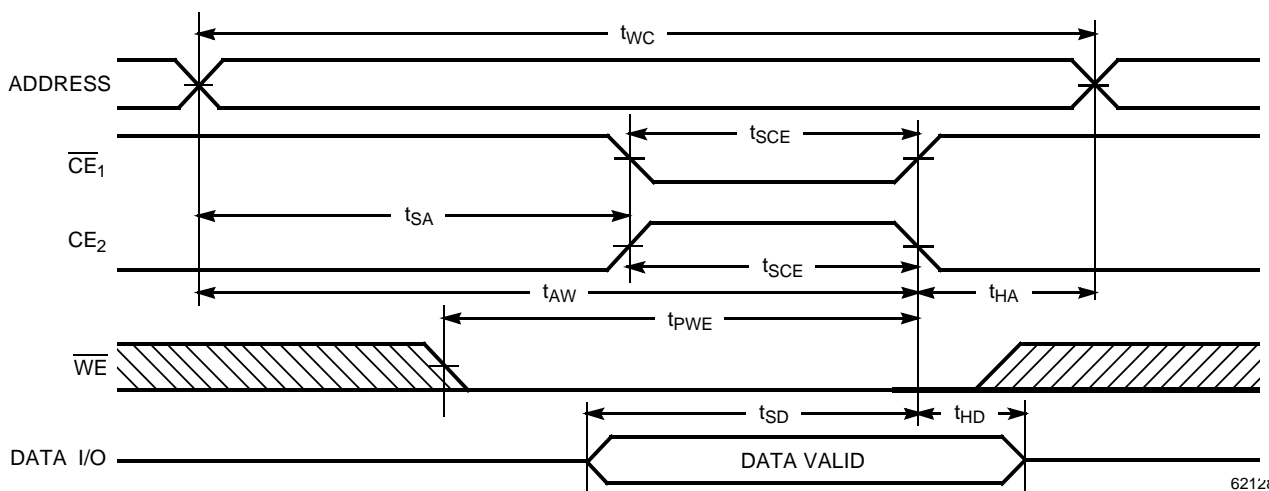
- Test conditions assume signal transition time of 5 ns or less timing reference levels of 1.5V, input pulse levels of 0 to 3.0V, and output loading of the specified I_{OL}/I_{OH} and 100-pF load capacitance.
- At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any given device.
- t_{HZOE}, t_{HZCE}, and t_{HZWE} are specified with C_L = 5 pF as in part (b) of AC Test Loads. Transition is measured ±200 mV from steady-state voltage.
- The internal write time of the memory is defined by the overlap of CE₁ LOW, CE₂ HIGH, and WE LOW. CE₁ and WE signals must be LOW and CE₂ HIGH to initiate a write and either signal can terminate a write by going HIGH. The data input set-up and hold timing should be referenced to the rising edge of the signal that terminates the write.
- The minimum write cycle time for write cycle #3 (WE controlled, OE LOW) is the sum of t_{HZWE} and t_{SD}.

Switching Waveforms
Read Cycle No. 1^[10, 11]


62128V-8

Read Cycle No. 2 (OE Controlled)^[11, 12]


62128V-9

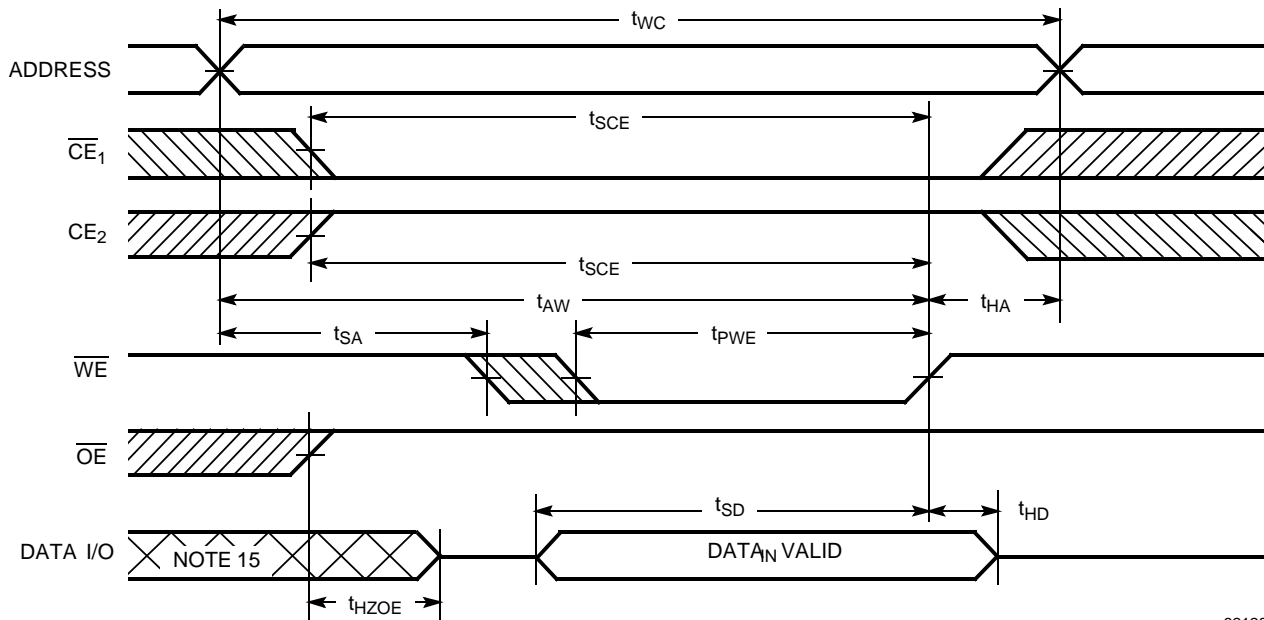
Write Cycle No. 1 (CE₁ or CE₂ Controlled)^[13, 14]


62128V-10

Notes:

10. Device is continuously selected. $\overline{OE}, \overline{CE} = V_{IL}, CE_2 = V_{IH}$.
11. \overline{WE} is HIGH for read cycle.
12. Address valid prior to or coincident with \overline{CE}_1 transition LOW and CE_2 transition HIGH.
13. Data I/O is high impedance if $\overline{OE} = V_{IH}$.
14. If \overline{CE}_1 goes HIGH or CE_2 goes LOW simultaneously with \overline{WE} HIGH, the output remains in a high-impedance state.

Switching Waveforms (continued)

Write Cycle No. 2 (\overline{WE} Controlled, \overline{OE} HIGH During Write)^[13, 14]


62128V-11

Truth Table

\overline{CE}_1	\overline{CE}_2	\overline{OE}	\overline{WE}	$I/O_0-I/O_7$	Mode	Power
H	X	X	X	High Z	Power-Down	Standby (I_{SB})
X	L	X	X	High Z	Power-Down	Standby (I_{SB})
L	H	L	H	Data Out	Read	Active (I_{CC})
L	H	X	L	Data In	Write	Active (I_{CC})
L	H	H	H	High Z	Selected, Outputs Disabled	Active (I_{CC})

Note:

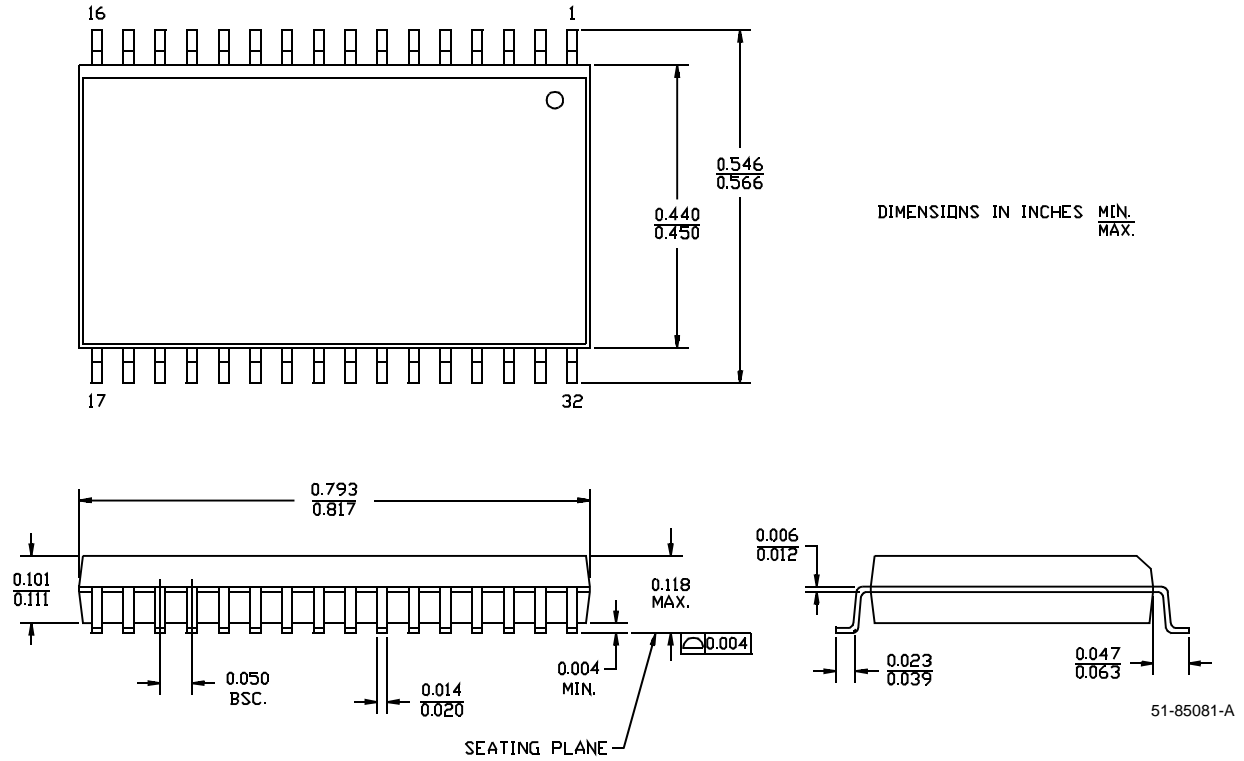
15. During this period, the I/Os are in output state and input signals should not be applied.

Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
55	CY62128VLL-55ZAI	ZA32	32-Lead STSOP Type 1	Industrial
70	CY62128VL-70SC	S34	32-Lead 450-Mil SOIC	Commercial
	CY62128VLL-70SC			
	CY62128VL-70ZC	Z32	32-Lead TSOP Type 1	
	CY62128VLL-70ZC			
	CY62128VL-70ZAC	ZA32	32-Lead STSOP Type 1	
	CY62128VLL-70ZAC			
	CY62128VLL-70ZRC	ZR32	32-Lead Reverse TSOP Type 1	
	CY62128VLL-70SI	S34	32-Lead 450-Mil SOIC	Industrial
	CY62128VL-70ZI			
	CY62128VLL-70ZI	Z32	32-Lead TSOP Type 1	
	CY62128VL-70ZAI			
	CY62128VLL-70ZAI	ZA32	32-Lead STSOP Type 1	
	CY62128VLL-70ZRI			
200	CY62128V18L-200ZC	Z32	32-Lead TSOP Type 1	Commercial
	CY62128V18L-200ZAI	ZA32	32-Lead STSOP Type 1	Industrial
	CY62128V18LL-200ZAI			

Package Diagrams

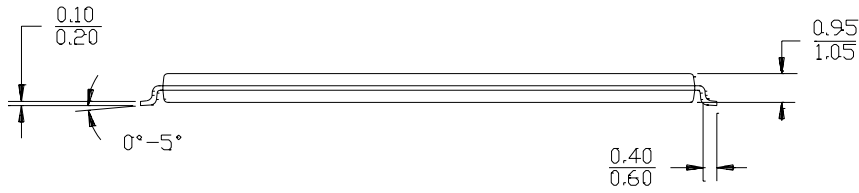
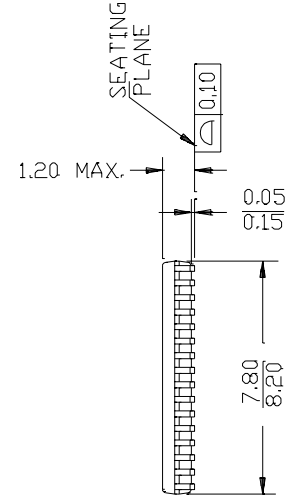
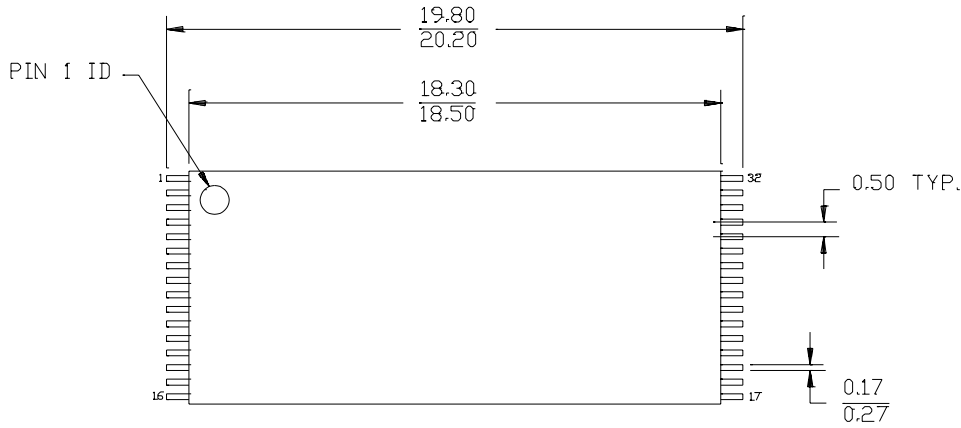
32-Lead (450 MIL) Molded SOIC S34



Package Diagrams

32-Lead Thin Small Outline Package Z32

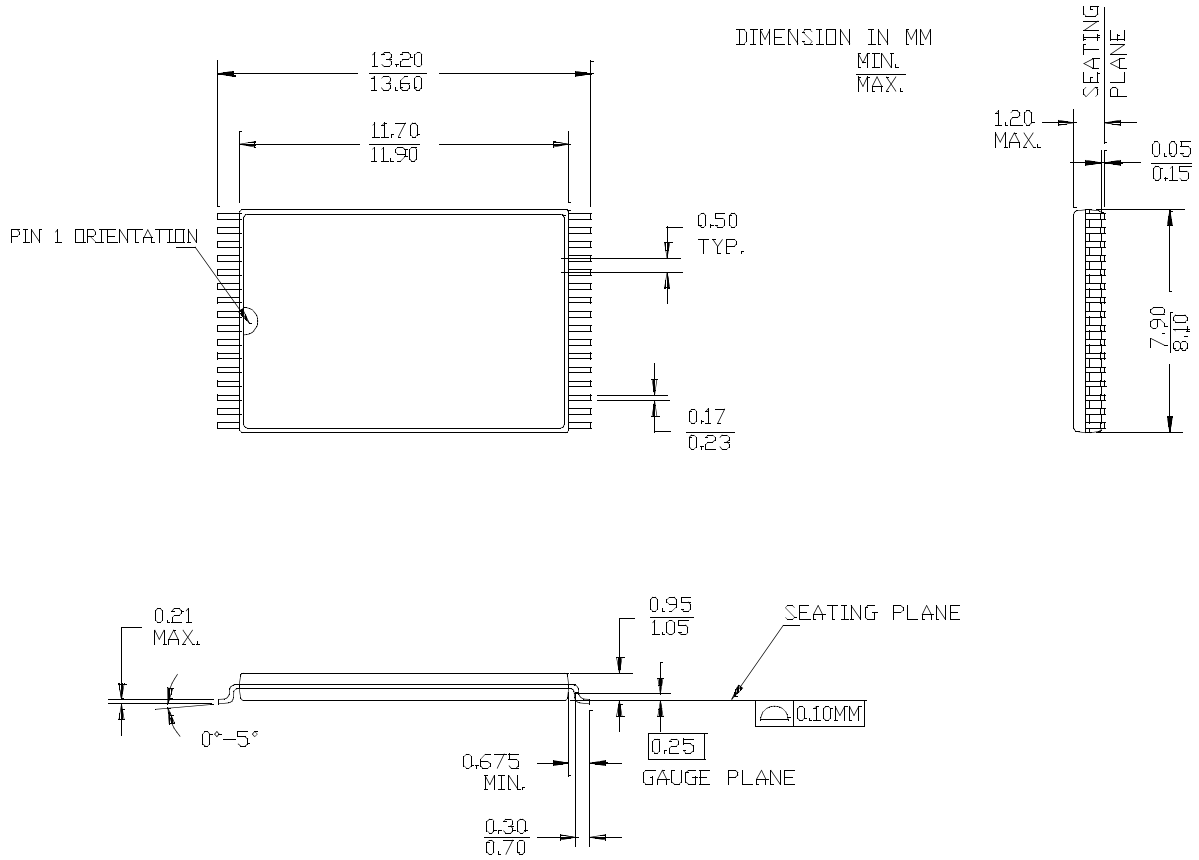
DIMENSION IN MM
MIN.
MAX.



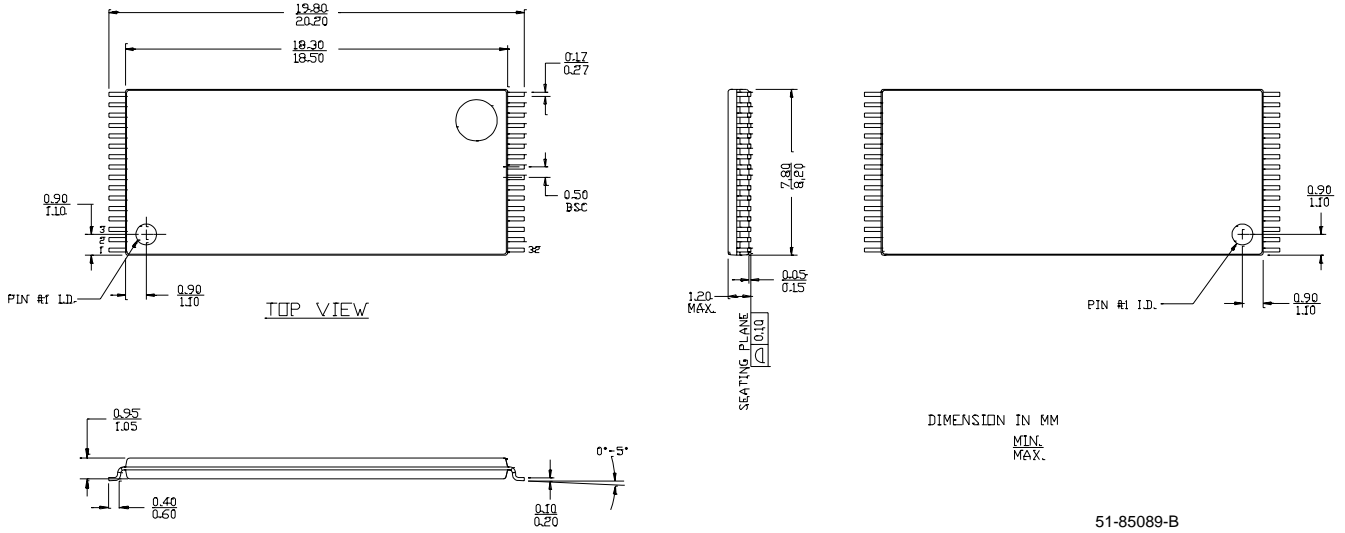
51-85056-C

Package Diagrams

32-Lead Shrunken Thin Small Outline Package ZA32



51-85094-C

Package Diagrams
32-Lead Reverse Thin Small Outline Package ZR32




Document Title: CY62128V Family 128K x 8 Static RAM Document Number: 38-05061				
REV.	ECN NO.	Issue Date	Orig. of Change	Description of Change
**	107252	09/10/01	SZV	Change Spec number from 38-00547 to 38-05061